



ESSCIRC/ESSDERC 2020 3D isotropic Hall sensor

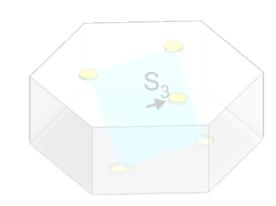
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Advanced Developments & Proof-of-Concepts TDK-Micronas, Freiburg, Germany laurent.osberger@micronas.com

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TDK Corporation – At a glance



TDK Corporation is a leading electronics company. Our focus is on information and communication technology, automotive, industrial and consumer electronics markets. TDK's comprehensive portfolio features passive components such as ceramic, aluminum electrolytic and film capacitors, magnetics, high-frequency, and piezo & protection devices. Our product spectrum also includes sensors and sensor systems such

as temperature and pressure, magnetic and MEMS sensors. In addition, TDK provides power supplies and energy devices, magnetic heads, and more. The portfolio is marketed under the product brands TDK, EPCOS, InvenSense, Micronas, Tronics and TDK-Lambda. The company has a network of design and manufacturing locations and sales offices in Asia, Europe, North and South America.

Key info (fiscal year 2020, ending March 31)		Major milestones	
Business	Passive componentsSensor application products	1935	TDK (Tokyo Denki Kagaku Kogyo = Tokyo Electric & Chemical Industries) established in Japan to manufacture and commercialize ferrites
	 Magnetic application products 	1986	SAE Magnetics acquired
	Energy application products	2005	Amperex Technology Limited (ATL) acquired
	Others	2005	Lambda Power Group acquired
Headquarters	Tokyo, Japan	2007	Recording Media business sold
Sales	JPY 1,363 billion	2008	EPCOS AG acquired
Sites	More than 200 factories, R&D & sales offices in more than 30 countries	2016	Micronas Semiconductor Holding AG acquired
		2017	TDK-Qualcomm HF joint venture RF360 started; cooperation with Qualcomm enhanced InvenSense, Inc. acquired
Employees	107,000	2018	Chirp Microsystems, Inc. acquired











TDK-Micronas



Glenrothes, Scotland TDK-Micronas Ltd.



- Hall ICs
- Embedded **Motor Controllers**

Leuven, Belgium **ICsense**



Analog, Mixed Signal and High Voltage ASICs

Freiburg, Germany **TDK-Micronas**



- Hall ICs
- Embedded ** CSENSE * MICRONAS **Motor Controllers**

ATD

&TDK

MSBG HQ

Saku / Nagano, Japan Asama Techno Factory (ATF)



- **TMR Sensors**
- Sensor Modules

TDK HQ

Tokyo, Japan



Dongguan, China SAE Magnetics LTD



- **TMR Sensors**
- Sensor Modules







***** MICRONAS







Product portfolio



- Magnetic sensor ICs
 - ¬ Hall switches (position, RPM)
 - ¬ 1D Hall sensor (position, angle, current, torque)
 - ¬ 3D Hall sensor (position, angle)
 - ¬ TMR sensor (position, angle, linear, current)
- Sensor modules
 - ¬ Stroke sensor
 - ¬ Current sensor
 - ¬ Speed sensor
- Embedded motor controllers ICs
 - Electric motor controllers (BDC, BLDC, stepper)
- Custom ICs (ICSense)
 - Analog, mixed signal and high voltage ASICs













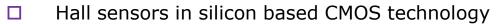


Hall sensor basics - LHS

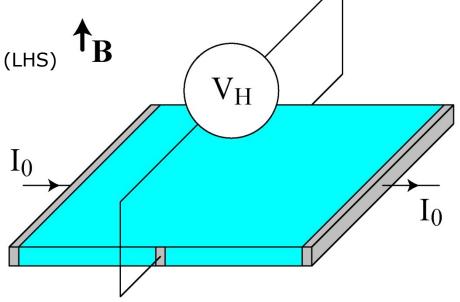


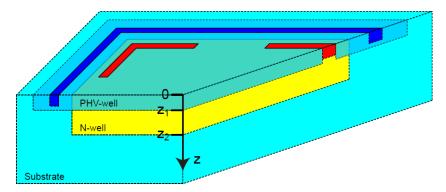
- Magnetic field **B** perpendicular to plate surface: Lateral Hall Sensor (LHS)
- ☐ Thin conductive plate with four electrical contacts
- \square Supply current I_0 between two opposite contacts
- \square Hall voltage $V_{\rm Hz}$ drops between remaining contacts

$$V_{Hz} = S_z B_z = \frac{r_H}{qnt} I_0 B_z$$



- Sensor active area realized by diffusion wells
 - \square Preferably low doped n-type material (\rightarrow high mobility)
 - ☐ Isolation using pn-junctions
- Electrical (n+-doped) contacts at the wafer surface
- Realistic device: Offset













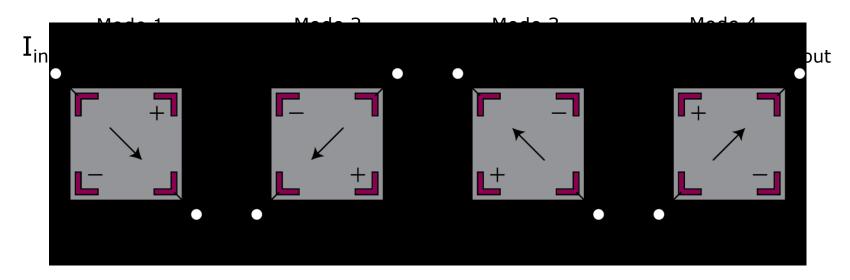


Hall sensor basics

Switching current



☐ Symmetric Hall plate design - 4 identical modes of operation



- □ Averaging of the Hall signal cancels out offsets due to
 - Geometry / material imperfections
 - Temperature gradients
 - Mechanical stress
- ☐ Magnetic response remains unaffected











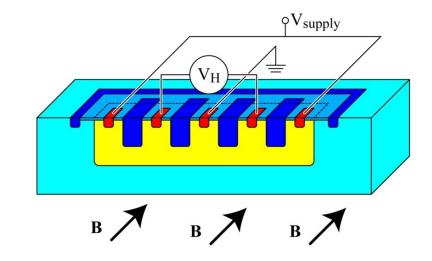


Hall sensor basics - VHS



- ☐ Magnetic field **B** in the plane of the chip: Vertical Hall sensor
 - Geometrical transformation of the LHS
 - Intrinsic lower sensitivity

- ☐ Five Contact (5C-)VHS in silicon based CMOS technology
 - Deep n-doped well (HV)
 - Five n+-doped contacts





3D magnetic field sensor: combination of a LHS and two VHS













Hall sensor basics - Pros/Cons







- ☐ Small size (~10...100µm edge length)
- Robustness (rather simple and stable physical effect)
- Large magnetic field range (highly linear, non-destructive)
- Direct integration with electronics allows
 - Signal amplification
 - Application specific (digital) signal processing
 - Compensation of parasitic effects

- ☐ Limited magnetic field resolution (~earth MF)
- ☐ Current consumption (~mA)
- Expensive compensation efforts
 - Probe / final testing with magnetic fields
- Cross-sensitivity on mechanical stress
 - Causes magnetic sensitivity drifts
- □ 3D sensors require two different sensing structures
 - Different characteristics
 - Sensitivity mismatch

Angular applications

angle
$$(\mathbf{B}) = \tan^{-1} \frac{B_x}{B_z} = \tan^{-1} \frac{V_{Hx} \cdot S_z}{V_{Hz} \cdot S_x} \approx \tan^{-1} \frac{V_{Hx}}{V_{Hz}}$$



3D isotropic Hall sensor









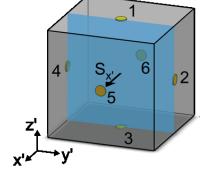


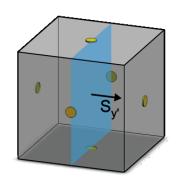
Hall sensor basics - 3DIH

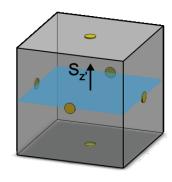


New generation of 3D magnetic field sensors allowing to sense the three components of the magnetic field with one sensitive element

- Cubic structure
 - 6 face-centered contacts
 - 3 virtual Hall planes (vHp)
 - Sensitivity vectors:
 - Mutually orthogonal
 - □ Same magnitude
 - Implementation would require sidewall contacts

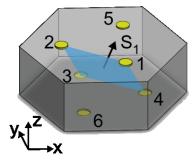


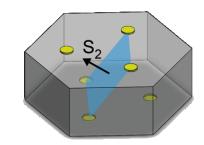


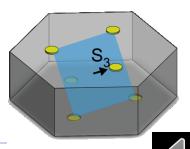




- ☐ Transformation of the cube: hexagonal prism
 - 6 contacts (front- and back-side)
 - 3 virtual Hall planes (vHp)
 - Sensitivity vectors:
 - ☐ Mutually orthogonal
 - ☐ Same magnitude













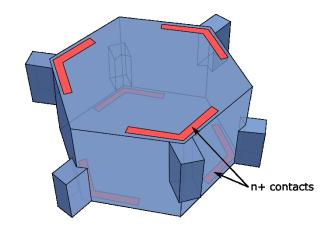


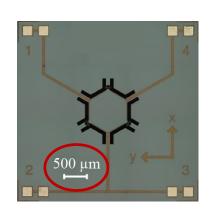
First prototype

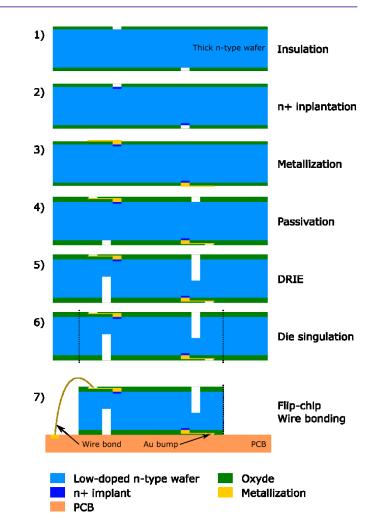


Main characteristics:

- Homogeneous low-doped n-type silicon wafer
- ☐ Hexagonal prism isolated by deep trenches from the substrate
- ☐ Mechanical and electrical interconnection using bridges
- □ n+ implantation and metallization on both sides of the wafer







[1] Christian Sander, Carsten Leube, Taimur Aftab, Patrick Ruther, Oliver Paul, "Monolithic Isotropic 3D Silicon Hall Sensor", Sensors and Actuators A: Physical, Volume 247, 2016, Pages 587-507











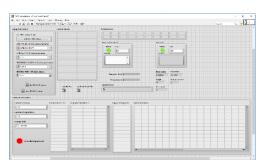
Experimental setup

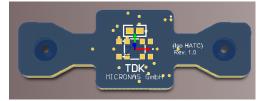


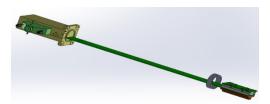
- Experimental electric/magnetic test bench integrated into existing TDK-Micronas lab environment
- 3D Helmholtz coil setup with stray field compensation
- 4-contact Kelvin measurements
- Controlled temperature





















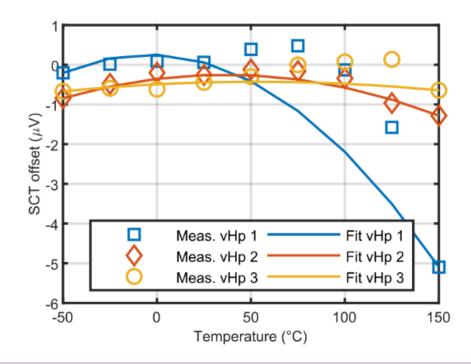


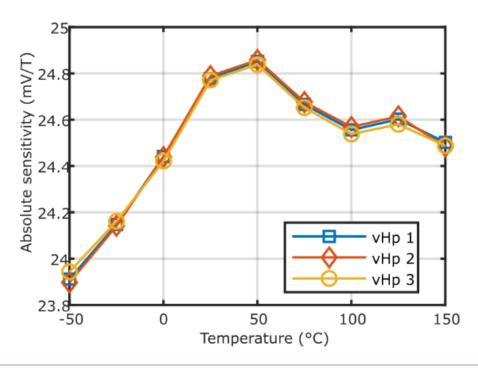


Measurement results



- ☐ Single mode offset in the mV range
- \square Residual offset after current switching in the μV range
- ☐ Sensitivity mismatch between vHps lower than 0.5% without calibration











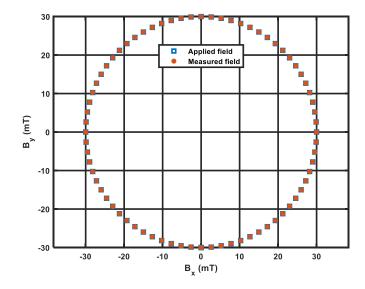


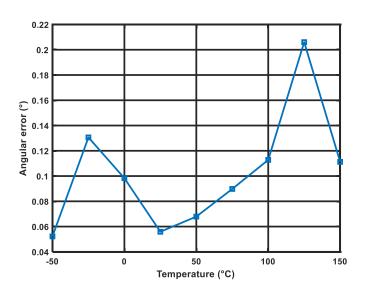


Measurement results



- ☐ Angular sensor application
- 30 mT rotating magnetic field
- ☐ Angular error (after calibration) lower than 0.2° over extended automotive temperature range

















Conclusion



- Promising prototype
- □ Lab-to-fab transition
 - Industrial process development
 - Scaling down the device to reduce power consumption
 - Combination with a specific ASIC platform











Acknowledgement



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